

## Relaxor ferroelectrics for neuromorphic computing

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**S** tructures **P**ropriétés **M**odélisation *des* S olides

Lontières

Context

Neuromorphic computing: Recreating brain functions using Artificial Neural Networks (ANN) and its hardware implementations. Essential units: neurons and synapses Conventional ANN: von-Neumann architecture, computing outside of memory, high energy consumption due to data transportation ("von-Neumann bottleneck") **Compute-in-memory (CIM):** emerging solution of the von-Neumann bottleneck









(b) paraelectric, and (c) ferroelectric materials

Requirements for analog states in crossbar device: nonvolatile, readily programmable, high ON/OFF ratio, long retention time, good endurance **Devices used in crossbar ANNs:** resistive devices, ferroelectric diodes, capacitive devices/ (most promising due to its near-zero static power)

## **State Establishment of Relaxor Ferroelectrics**

The evaluation of the state establishment ability of PZN-4.5PT was performed. Four consecutive pulse trains with the amplitude of [-100V, 100V, -100V, 100V] and the width of 10ms were applied to the material.

**Relaxor ferroelectrics**: a category of ferroelectric materials with with strong electric field instabilities, permitting readily state programming **Representative RFEs:** PMN, PZN, PMN-xPT, PZN-xPT, PLZT...





Left: The evaluation of dielectric permittivity of  $Pb(Zn_{1/3}Nb_{2/3})O_3-4.5PbTiO_3$  (PZN-4.5PT) under DC sweep

**Right: Evaluation of device capacitance under** two consecutive DC sweeps between [-200V, 200V]

**Observation:** RFEs like PZN-PT can exhibit multiple nonvolatile and readily programmable capacitive states, giving it great potential to be used in neuromorphic computing

**Relaxor Ferroelectrics in Neural Networks** 







Evaluation of device linearity. LTP: long-term potentiation, LTD: longterm depression, corresponding to the staged increase/decrease of device polarization, respectively

**Observations:** 

(1) PZN-4.5PT demonstrates distinct long-term potentiation (LTP) and long-term depression (LTD) behavior, showing the ability of manageably updating device state and mimicking the biological synapses of human brain;

(2) PZN-4.5PT shows the ability to access multiple polarization states by simply changing the profile of applied electric pulse;

(3) The linearity factor A of PZN-4.5PT is derived from [3,4]

$$P_{LTP} = B\left(1 - \exp\left(-\frac{N}{A}\right)\right) + P_{min}$$
$$P_{LTD} = -B\left(1 - \exp\left(-\frac{N - N_{max}}{A}\right)\right) + P_{max}$$



Integration of signals for PZN-4.5PT under different electric fields, resembles the dendrite in the human brain





where P stands for device polarization, N stands for number of pulses, and  $P_{min}$ ,  $P_{max}$ and  $N_{max}$  were extracted from the experimental data.

The calculated A equals to 1.28 for long-term potentiation (LTP) and -2 for long-term depression, ensuring relatively low accuracy degradation during the learning works [4]. From the observation above, we can conclude that PZN-4.5PT is a potential candidate for neuromorphic computing.

Comparison of the recognition accuracies for the simplified SVHN dataset in a neural network [5] with three different dendrites. w/o: test accuracy of the network without dendrite [5]

Reservoir node	Test error	<b>a</b> 1	a <sub>2</sub>	a <sub>3</sub>	<i>a</i> <sub>4</sub>
[6]	0.7944	0.96	1.0	0.9867	1.0
PZN-4.5PT	0.7343	1.0	1.0	0.9933	1.0

Comparison of the performance of a reservoir system [6] on dynamic gestion recognition (DGR) with different reservoir node. *a<sub>i</sub>*: The recognition accuracy of the *i*-th gesture.

[1] Von Neumann architecture. *Wikipedia* (2022) [2] D. Joksas, A. Mehonic. *SoftwareX*, **12**, 100617 (2020) [3] W.-Q. Zhang *et al. Nat. Electron*, **3(7)**, **2022** 

[4] P.-Y. Chen *et al. 2017 IEDM*, **6.1.1-6.1.4** (2017) [5] X. Li et al., *Nat. Nanotechnol.*, **15**, 776 (2020) [6] Y. Zhong et al., *Nat. Electron.*, **5**, 672-681 (2022)